

Fig. 1

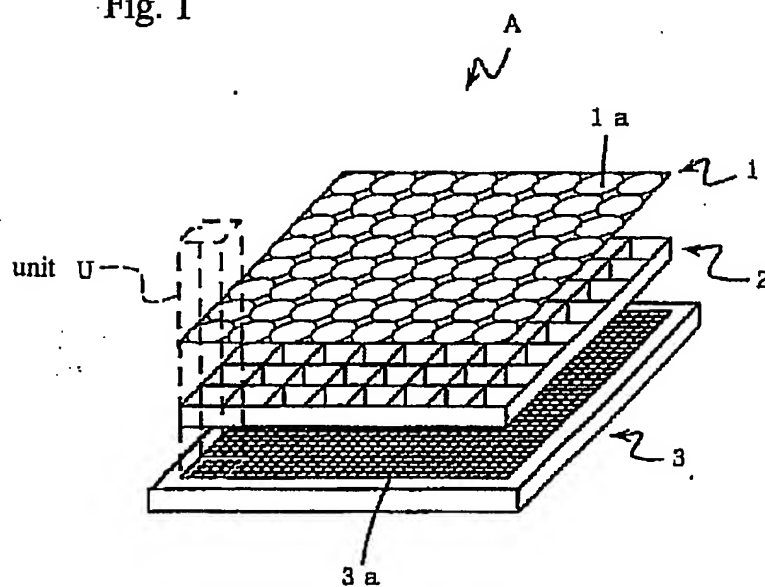


Fig. 2

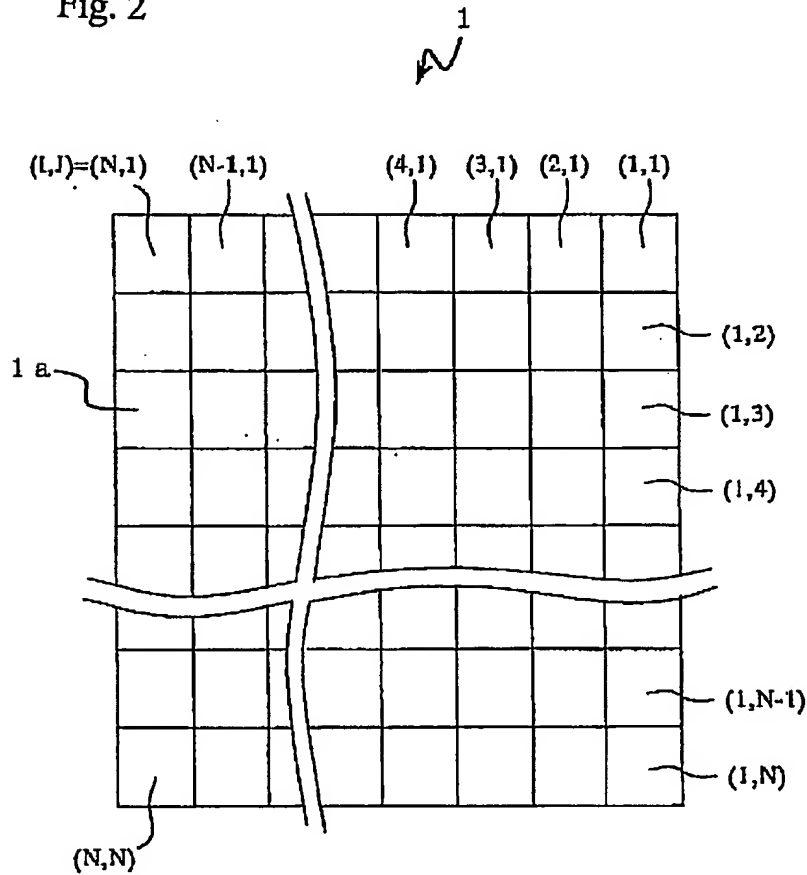


Fig. 3

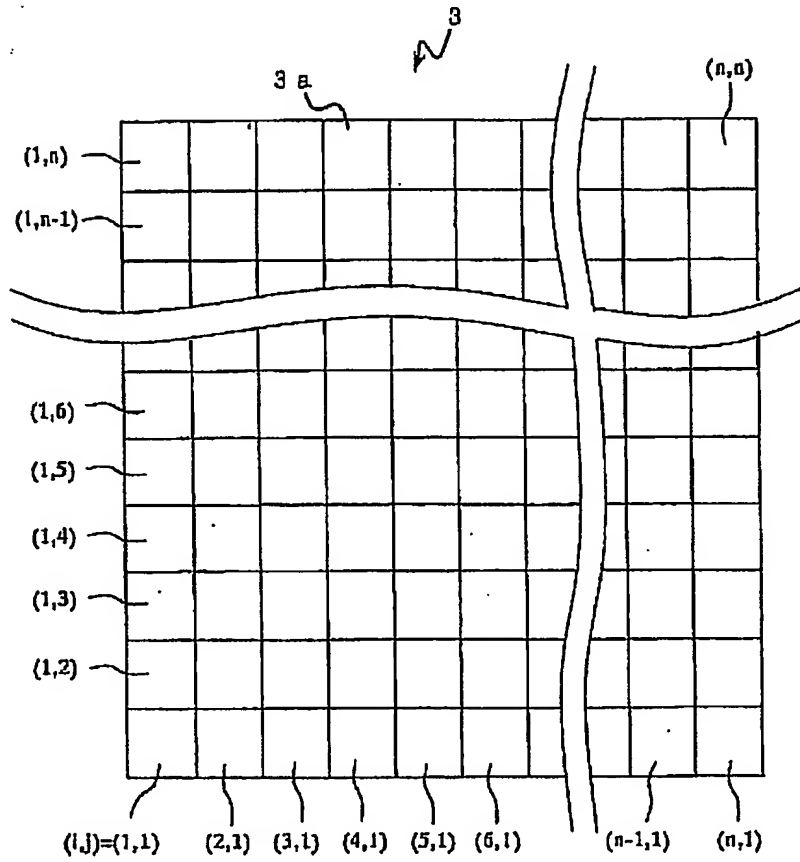


Fig. 4

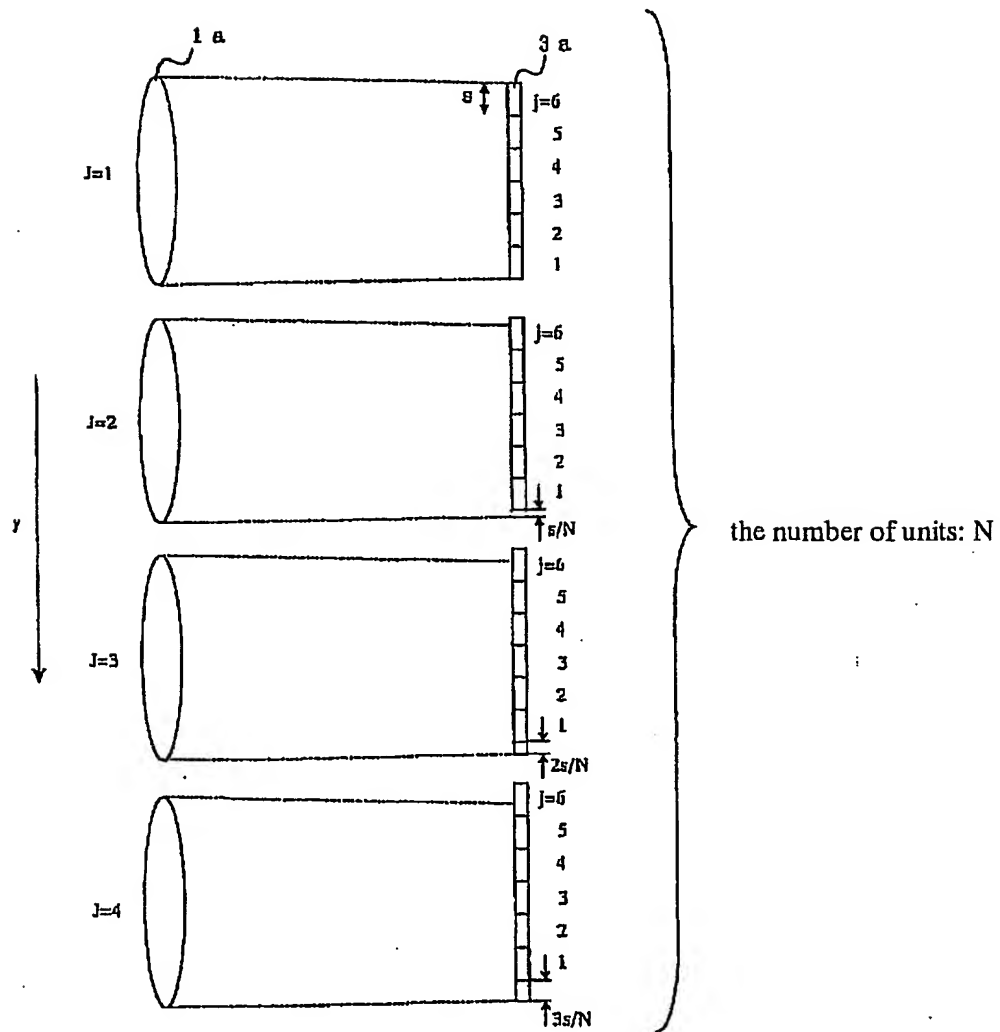
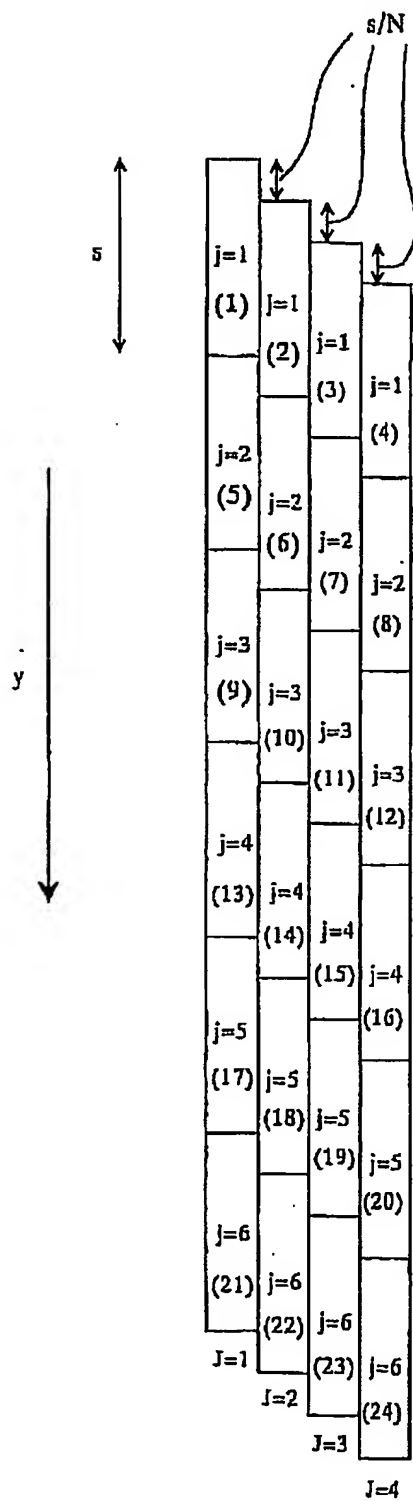


Fig. 5



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Fig. 6

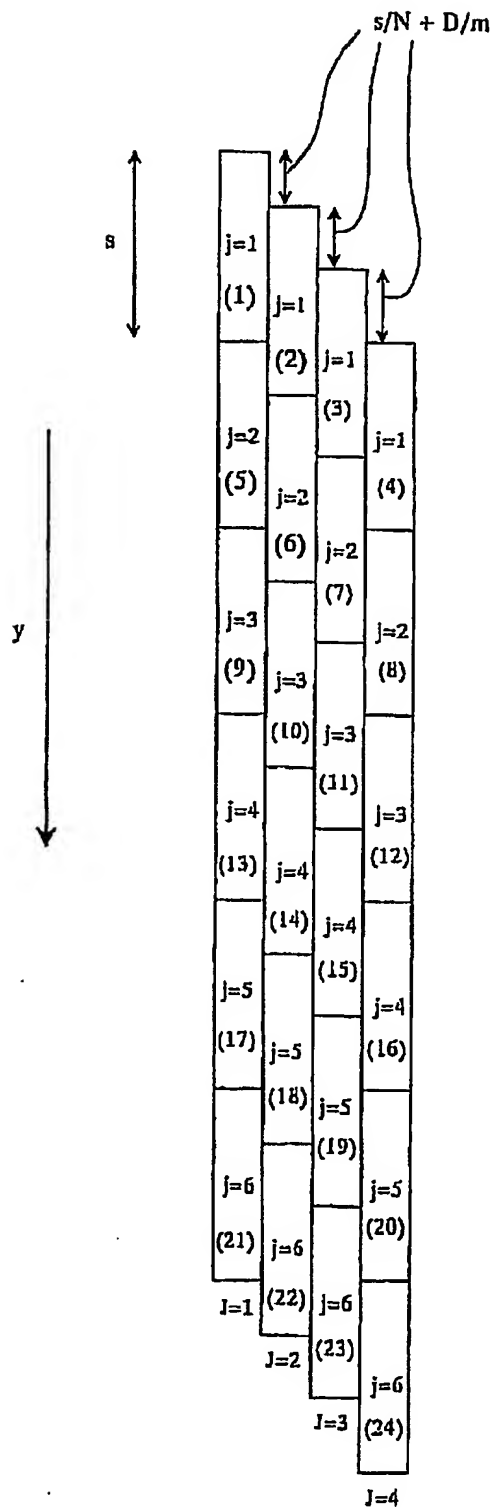


Fig. 7

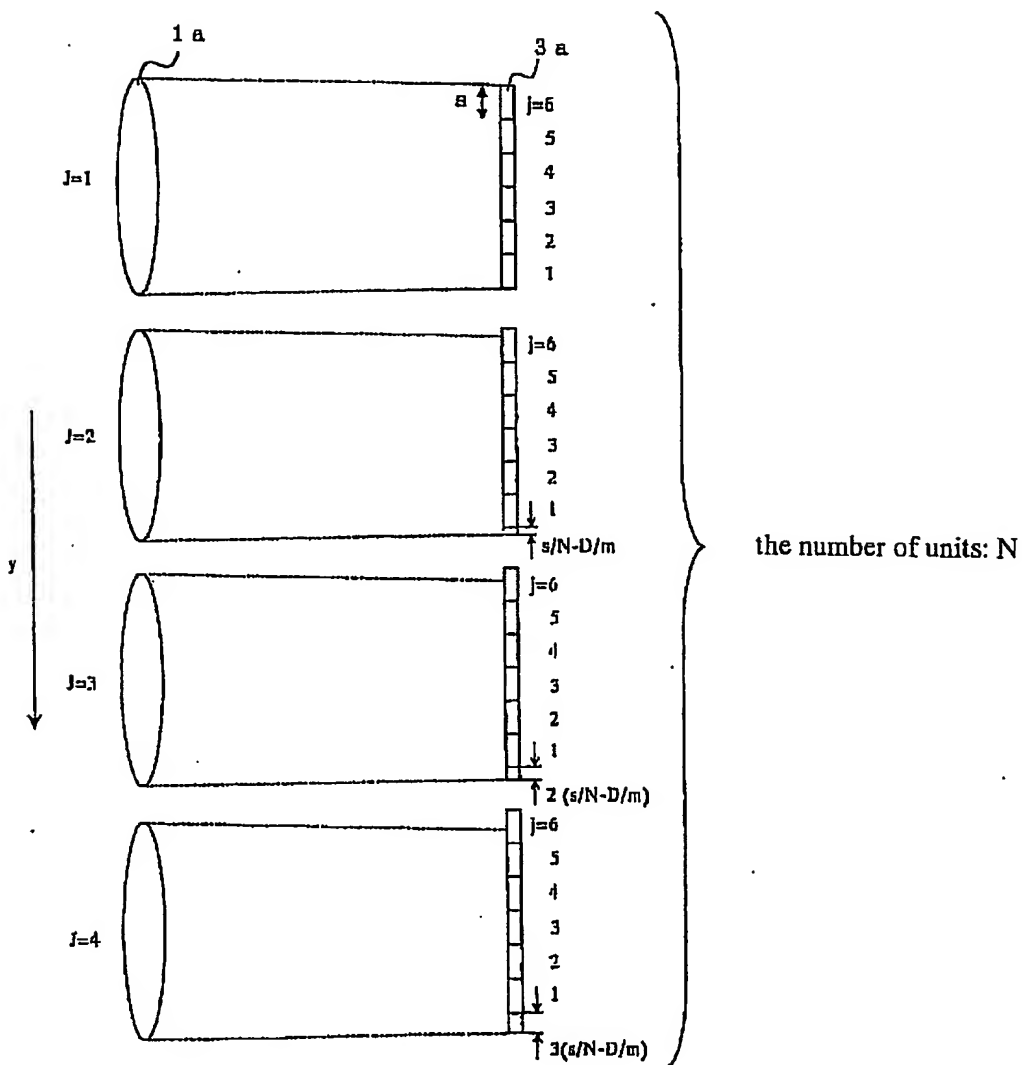


Fig. 8

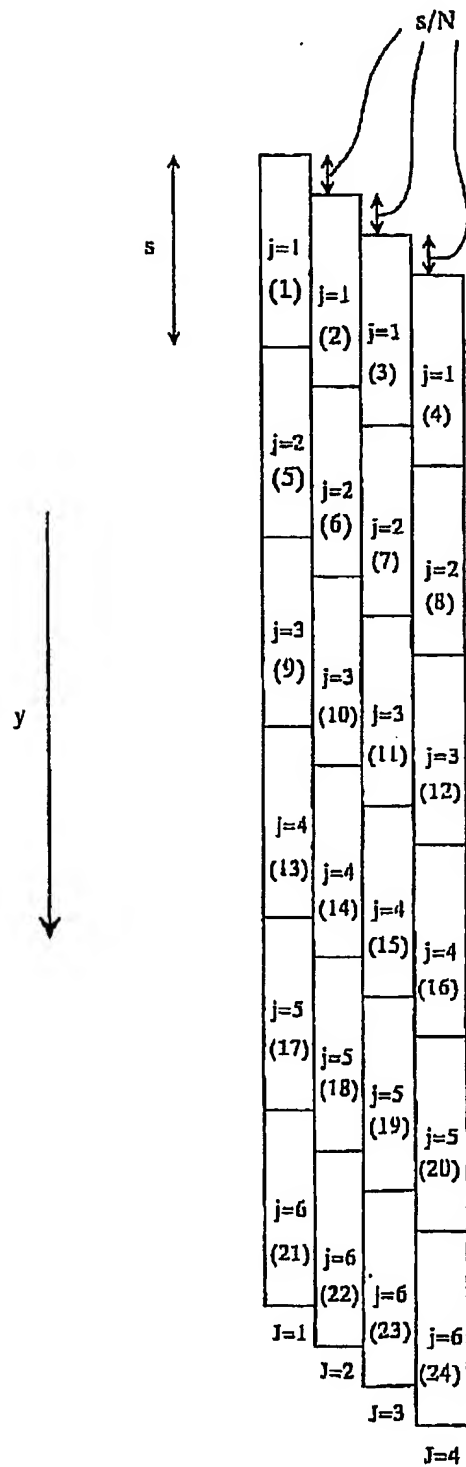


Fig. 9

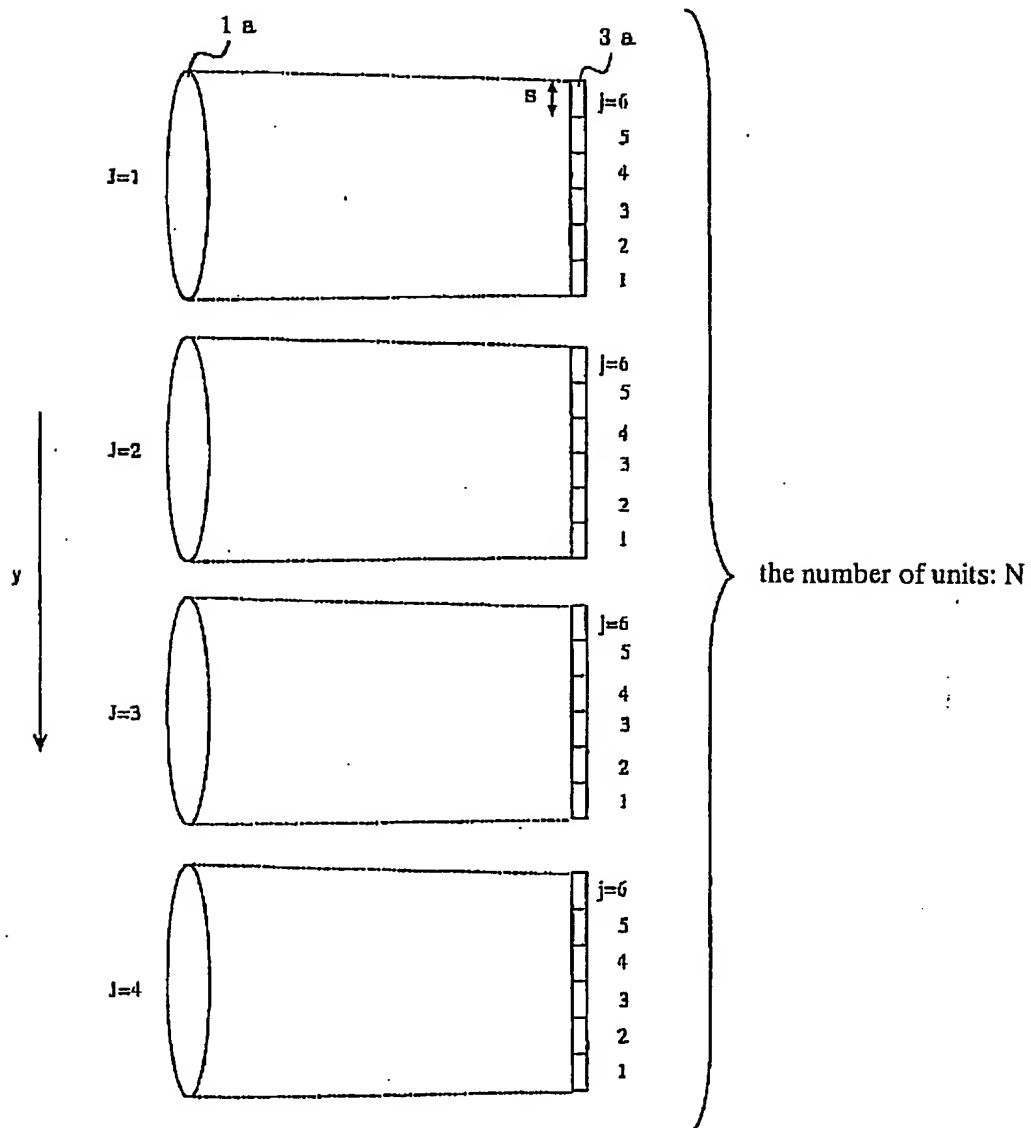


Fig. 10

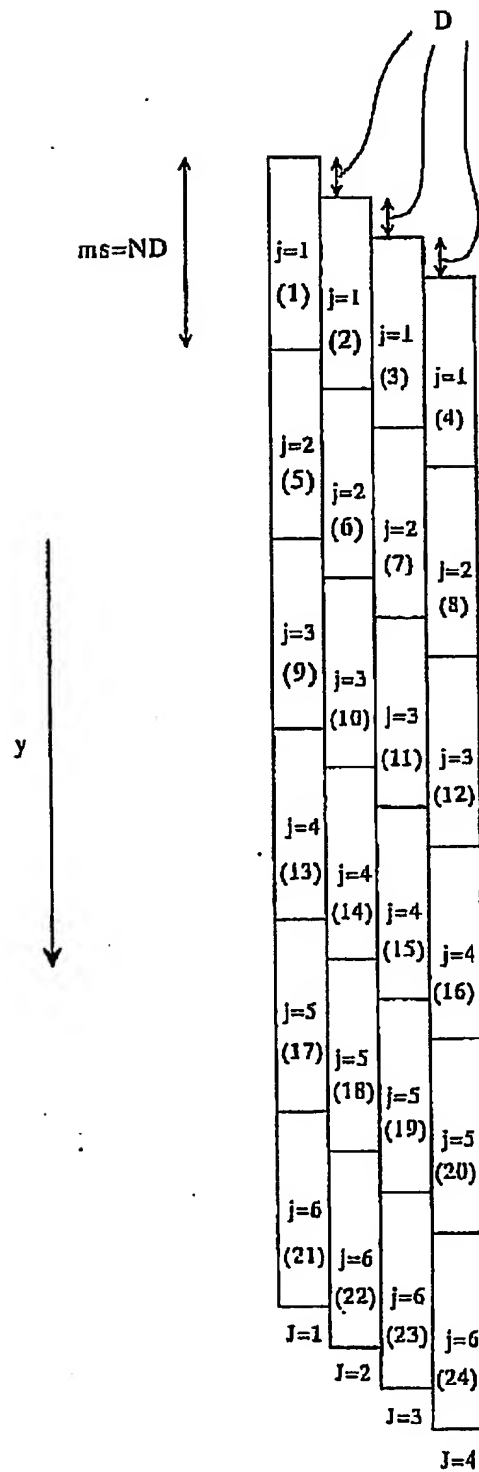
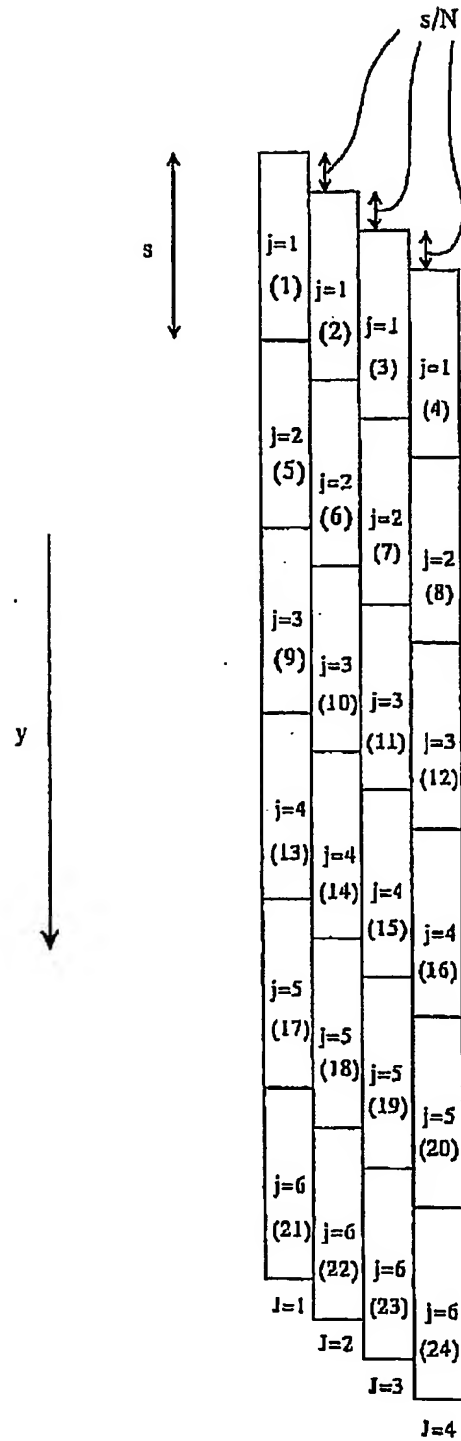


Fig. 11



The diagram shows a grid structure with labels (i,j) and (n,n) . The grid is divided into four quadrants by a vertical line and a horizontal line. The top-left quadrant contains labels $(1,n)$ and $(1,n-1)$. The top-right quadrant contains label (n,n) . The bottom-left quadrant contains labels $(1,6)$, $(1,5)$, $(1,4)$, $(1,3)$, and $(1,2)$. The bottom-right quadrant contains labels $(n-1,1)$ and $(n,1)$. The grid is composed of cells, some of which are labeled with 'G' and 'R'. A label '3' is positioned above the grid, and a label '3 a' is positioned to the left of the grid.

Figure 3 is a schematic diagram of a grid structure, likely representing a semiconductor device layout. The grid is divided into two main sections by a vertical line. The left section is labeled '3 a' and the right section is labeled '3'. The grid is composed of cells, some of which are labeled with 'Mg', 'G', 'Cy', and 'Ye'. The grid is indexed by rows (1, n) to (1, 2) on the left and columns (1, 1) to (n, 1) at the bottom. A thick horizontal line separates the top and bottom parts of the grid.